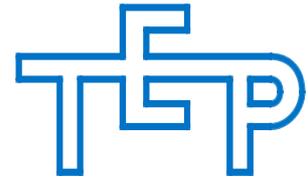




SISPAD
Companion Workshop
and Forum for Discussion



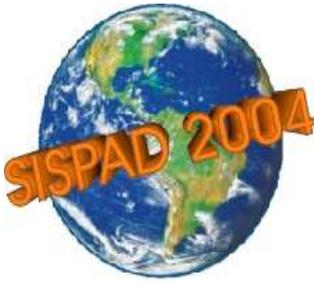
From Sub- μ m-CMOS to Nanotechnology

Munich University of Technology,
Main Campus, North Buildings, Building N4
Sunday, September 5, 2004
9:00 to 16:40

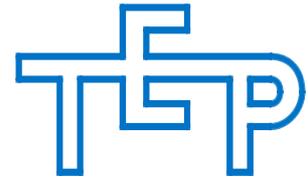
Workshop Presentations

- 9:00 *Welcome*
- 9:10 Peter Voigt, Infineon Technologies AG, München, Germany:
“Process and Device Simulation for the Development of Advanced
DRAM Technologies”
- 10:00 Hans Kosina, Institute for Microelectronics, Technical University of
Vienna, Austria:
“Advanced Transport Models for Nanodevices”
- 10:50 *Break*
- 11:20 Frederik Heinz, Integrated Systems Laboratory, ETH Zürich,
Switzerland:
“Simulation Models for Semiconductor Nanodevices”
- 12:10 *Lunch*
- 13:40 Wolfgang Windl, Ohio State University, Columbus, Ohio, USA:
“Ab-initio Assisted Process and Device Simulation for Nanodevices”
- 14:30 Joachim Piprek, University of California, Santa Barbara, CA, USA:
“Modeling and Simulation of Quantum Well Devices in
Optoelectronics”
- 15:20 *Break*
- 15:50 Lukas Worschech, Justus-Maximilians-Universität Würzburg,
Germany:
“Ballistic Nanodevices in the Non-linear Regime”
- 16:40 *End of workshop*

Organizers: Gerhard Wachutka, Gabriele Schrag (TUM)



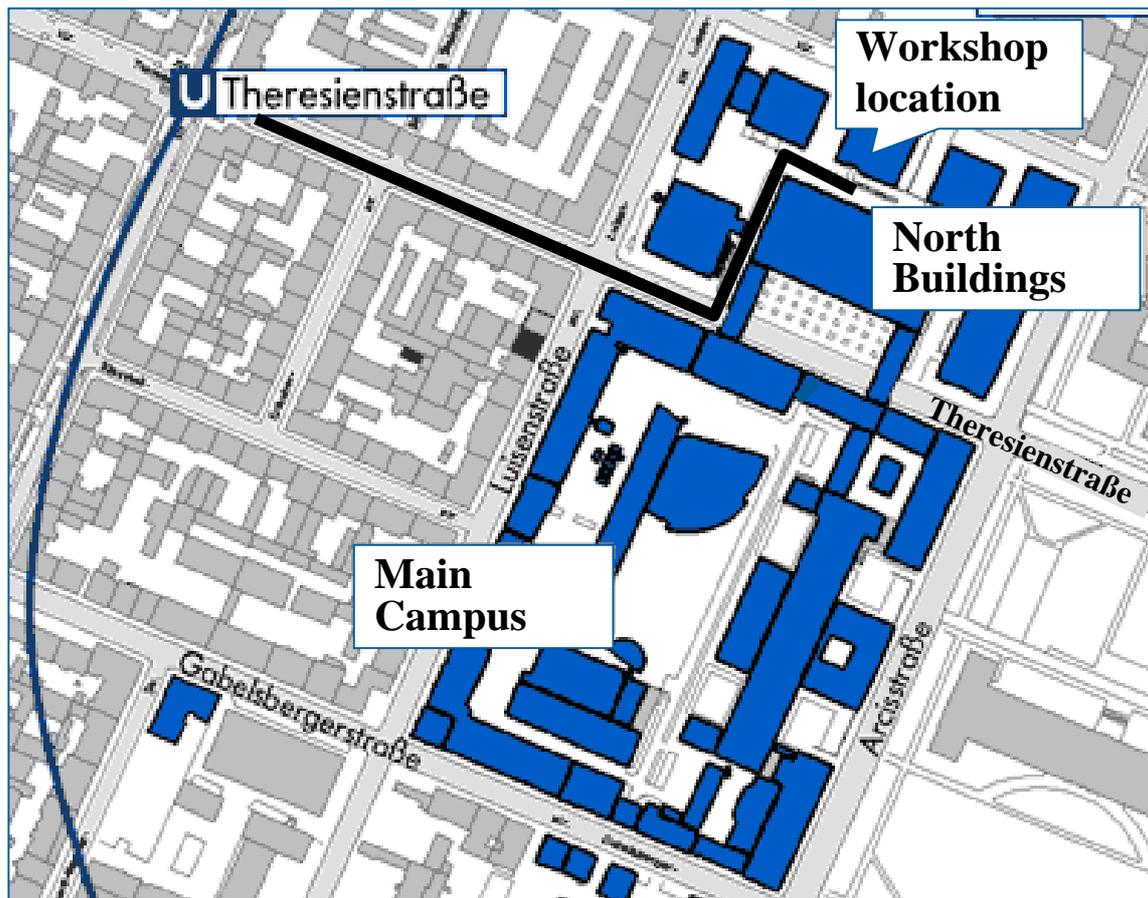
SISPAD
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Registration:

The registration fee is € 100 and includes workshop documents, coffee breaks, and lunch. To register visit <http://www.tep.ei.tum.de/sispad04>.

How to get to the workshop location:



Take any of the westbound S-trains in direction of “Hauptbahnhof” (main station). Get off there and change to underground line U2, northbound to destination “Feldmoching”. After two stops get off at “Theresienstraße” and follow the exit signs to “Technische Universität München”. Follow the way indicated in the map above.